

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT

In re application of: Kapre, et al

Attorney Docket No.: 01-721/LSI1P185

Application No.: 10/020,304

Examiner: Sefer, Ahmed N.

Filed: December 13, 2001

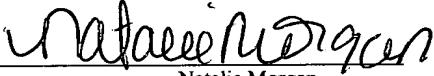
Group: 2826

**Title: BURIED CHANNEL DEVICES AND A
PROCESS FOR THEIR FABRICATION
SIMULTANEOUSLY WITH SURFACE
CHANNEL DEVICES TO PRODUCE
TRANSISTORS AND CAPACITORS WITH
MULTIPLE ELECTRICAL GATE OXIDES**

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as First
Class Mail to: Commissioner for Patents, Washington,
DC 20231 on November 22, 2002.

Signed:


Natalie Morgan

AMENDMENT B

Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

This amendment and the enclosed remarks are submitted in response to the
Non-Final Office Action mailed on July 22, 2002. Applicants respectfully request
reconsideration of the captioned application in view of the following remarks and
amendments.

In the Claims:

Please amend the claims as follows (a version of the amended claims showing
the changes made accompanies this response in an Appendix):

B1 1. (Once Amended) ~~In a semiconductor device having at least an insulating gate dielectric layer and a gate fabricated upon a semiconductor substrate, a buried channel implanted below the insulating gate dielectric layer, the buried channel being doped with a predetermined dopant and a peak concentration of the dopant positioned at a~~



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Robert
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and

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